

NPN SILICON PLANAR MEDIUM POWER
DARLINGTON TRANSISTOR

ZTX614

ISSUE 1 – APRIL 94

FEATURES

- * 100 Volt V_{CEO}
- * 800 mA continuous current
- * Gain of 10K at $I_C=500mA$
- * $P_{tot}=1$ Watt

REFER TO BCX38 FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	10	V
Continuous Collector Current	I_C	800	mA
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	P_{tot}	1.0 5.7	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120			V	$I_C=10\mu A, I_E=0$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	100			V	$I_C=10mA, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=10\mu A, I_C=0$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB}=60V, I_E=0$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB}=8V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1.25	V	$I_C=800mA, I_B=8mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.8	V	$I_C=800mA, V_{CE}=5V^*$
Static Forward Current Transfer Ratio	h_{FE}	5000 10000				$I_C=100mA, V_{CE}=5V^*$ $I_C=500mA, V_{CE}=5V^*$

*Measured under pulsed conditions. Pulse Width=300 μs . Duty cycle $\leq 2\%$

查询ZTX614供应商

捷多邦，专业PCB打样工厂，24小时加急出货